

DIGITRON SEMICONDUCTORS

BTC08-(A) SERIES

SILICON BIDIRECTIONAL THYRISTORS

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage ⁽¹⁾ ($T_J = 110^\circ\text{C}$) BTC08-100(A) BTC08-200(A) BTC08-400(A) BTC08-600(A)	V_{DRM}	100 200 400 600	Volts
RMS on-state current ($T_C = 72^\circ\text{C}$)	$I_{\text{T(RMS)}}$	8.0	Amps
Peak surge current (1 cycle, 50Hz, $T_J = -40$ to $+110^\circ\text{C}$)	I_{TSM}	60	Amps
Circuit fusing considerations ($T_J = -40$ to 110°C , $t = 10\text{ms}$)	I^2t	18	A^2s
Peak gate power (pulse width = $10\mu\text{s}$)	P_{GM}	10	Watts
Average gate power ($T_C = 80^\circ\text{C}$, $t = 10\text{ms}$)	$P_{\text{G(AV)}}$	0.5	Watts
Peak gate current (pulse width = $10\mu\text{s}$)	I_{GM}	3.5	Amps
Operating junction temperature range	T_J	-40 to +110	$^\circ\text{C}$
Storage temperature range	T_{stg}	-40 to +150	$^\circ\text{C}$
$I_{\text{TM}} = 12\text{A}$, $I_{\text{G}} = 200\text{mA}$	di/dt	10	$\text{A}/\mu\text{s}$

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage.

Note 2: Soldering temperatures shall not exceed 200°C for 10 seconds.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	$R_{\theta\text{JC}}$	2.2	$^\circ\text{C}/\text{W}$
Thermal resistance, junction to ambient	$R_{\theta\text{JA}}$	60	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ.	Max	Unit
Peak blocking current (either direction) (Rated V_{DRM} @ $T_J = 110^\circ\text{C}$, gate open)	I_{DRM}	-	-	1.0	mA
Peak on-state voltage (either direction) ($I_{\text{TM}} = 10\text{A}$ peak)	V_{TM}	-	1.5	1.75	Volts
Gate trigger voltage (continuous dc) (main terminal voltage = 12V, $R_L = 100\Omega$) All types, all quadrants (main terminal voltage = rated V_{DRM} , $R_L = 10\text{k}\Omega$, $T_J = 110^\circ\text{C}$) All types, all quadrants	V_{GTM}	- 0.2	- -	2.5 -	Volts
Holding current (either direction) (main terminal source voltage = 12V, gate open, initiating current = 1.0A) $T_C = -40^\circ\text{C}$ $T_C = 25^\circ\text{C}$	I_{H}	- -	- -	100 45	mA
Latching current (main terminal source voltage = 24V, gate trigger source = 15V, 100Ω) MT2(+), G(+) MT2(-), G(-) MT2(+), G(-)	I_{L}	- - -	- - -	100 100 200	mA

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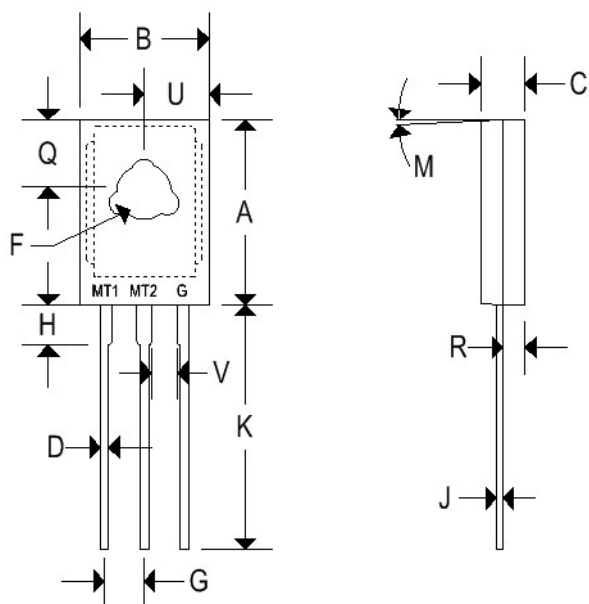
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Characteristic	Symbol	Min	Typ.	Max	Unit
Critical rate of rise of off-state voltage (Rated V_{DRM} , exponential voltage rise, gate open, $T_C = 100^\circ\text{C}$)	dv/dt	50	100	-	V/ μs
Blocking voltage application rate at commutation (@ V_{DRM} , gate open commutating di/dt = 3.2A/ms)	dv/dt(c)	4	-	-	V/ μs

Characteristic	Symbol	QUADRANT			
		I mA	II mA	III mA	IV mA
Peak gate trigger current (main terminal voltage = 12V, $R_L = 100\Omega$) BTC08 SERIES, $T_J = 25^\circ\text{C}$ BTC08 SERIES, $T_J = -40^\circ\text{C}$ BTC08-(A) SERIES, $T_J = 25^\circ\text{C}$ BTC08-(A) SERIES, $T_J = -40^\circ\text{C}$	I_{GTM}	50 100 50 100	50 100 50 100	50 100 50 100	- - 100 200

MECHANICAL CHARACTERISTIC

Case	TO-220AB
Marking	Body painted, alpha-numeric
Pin out	See below



	TO-220AB			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.575	0.620	14.600	15.750
B	0.380	0.405	9.650	10.290
C	0.160	0.190	4.060	4.820
D	0.025	0.035	0.640	0.890
F	0.142	0.147	3.610	3.730
G	0.095	0.105	2.410	2.670
H	0.110	0.155	2.790	3.930
J	0.014	0.022	0.360	0.560
K	0.500	0.562	12.700	14.270
L	0.045	0.055	1.140	1.390
N	0.190	0.210	4.830	5.330
Q	0.100	0.120	2.540	3.040
R	0.080	0.110	2.040	2.790
S	0.045	0.055	1.140	1.390
T	0.235	0.255	5.970	6.480
U	-	0.050	-	1.270
V	0.045	-	1.140	-
Z	-	0.080	-	2.030

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FIGURE 1 – RMS CURRENT DERATING (f = 50 Hz)

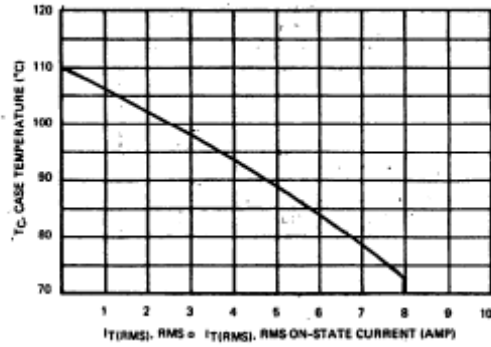


FIGURE 2 – MAXIMUM ON-STATE CHARACTERISTICS

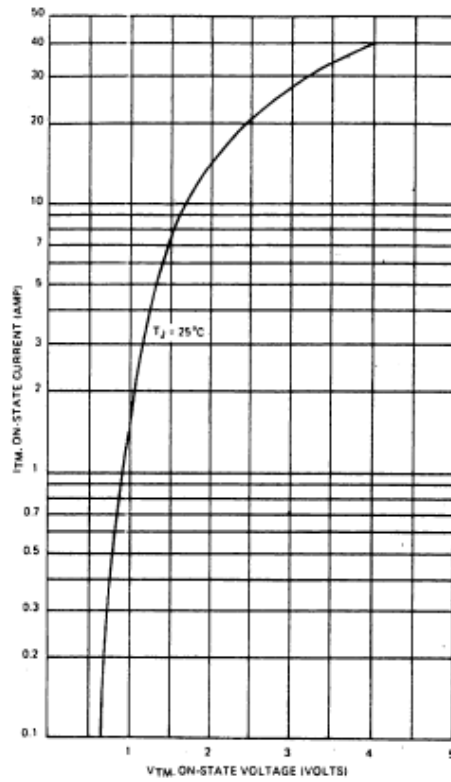
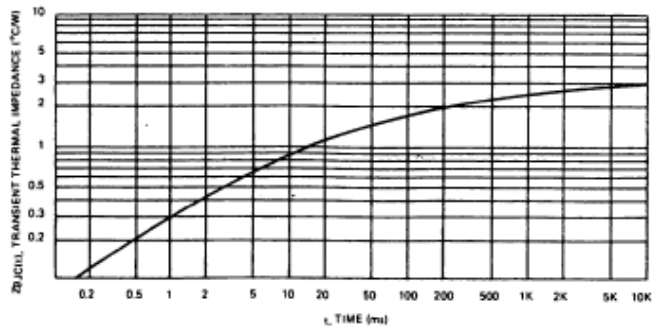


FIGURE 3 – THERMAL RESPONSE



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FIGURE 4 – TYPICAL HOLDING CURRENT

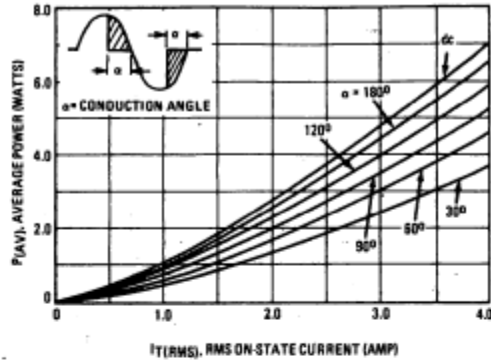


FIGURE 5 – TYPICAL GATE-TRIGGER VOLTAGE

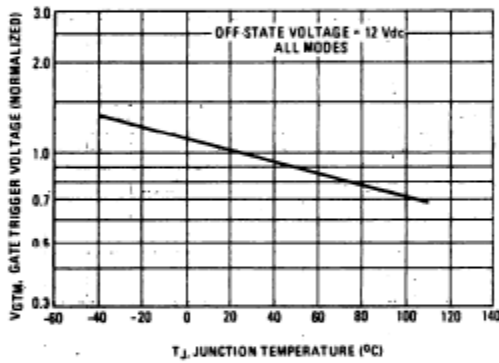


FIGURE 6 – TYPICAL GATE-TRIGGER CURRENT

